Octal Bus Buffer

The MC74VHC244 is an advanced high speed CMOS octal bus buffer fabricated with silicon gate CMOS technology.

The MC74VHC244 is a noninverting 3-state buffer, and has two active-low output enables. This device is designed to be used with 3-state memory address drivers, etc.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

- High Speed: $t_{PD} = 3.9 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 4 \mu A \text{ (Max)}$ at $T_A = 25 \text{ °C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.9 \text{ V (Max)}$
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model > 2000 V Machine Model > 200 V
- Chip Complexity: 136 FETs
- Pb-Free Packages are Available*

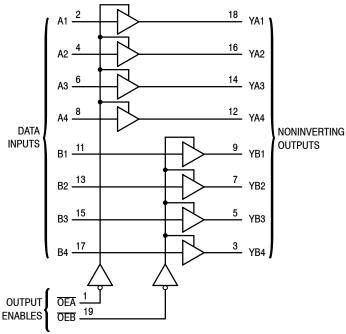


Figure 1. Logic Diagram



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MARKING DIAGRAM



SOIC-20 WB DW SUFFIX CASE 751D



TSSOP-20 DT SUFFIX CASE 948E



20 RAAAAAAAAAA VHC 244 O ALYW 1 HUHUHUHUH



SOIC EIAJ-20 M SUFFIX CASE 967 A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year

WW, W = Work Week

PIN ASSIGNMENT

OEA [1●	20	v _{cc}
A1 [2	19) OEB
YB4	3	18	YA1
A2 [4	17] B4
ҮВ3 [5	16	YA2
A3 [6	15] B3
YB2	7	14	YA3
A4 [8	13] B2
YB1 [9	12	YA4
GND [10	11] B1

ORDERING INFORMATION

See detailed ordering and shipping information in the Ordering Information Table on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

FUNCTION TABLE

INP	OUTPUTS	
OEA, OEB	A, B	YA, YB
L	L	L
L	Н	Н
н	X	Z

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74VHC244DW - OBSOLETE*	SOIC-20 WB	38 Units/Rail
MC74VHC244DWR2	SOIC-20 WB	1000/Tape & Reel
MC74VHC244DT	TSSOP-20 (Pb-Free)	75 Units/Rail
MC74VHC244DTR2	TSSOP-20 (Pb-Free)	2500/Tape & Reel
MC74VHC244M - OBSOLETE*	SOIC EIAJ-20 (Pb-Free)	1600 Units/Box
MC74VHC244MEL	SOIC EIAJ-20 (Pb-Free)	2000/Tape & Reel

^{*}This device is obsolete, information available for reference.

MAXIMUM RATINGS (Note 1)

Symbol	!	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	Digital Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage		-0.5 to V _{CC} +0.5	V
I _{IK}	Input Diode Current		-20	mA
lok	Output Diode Current		± 20	mA
I _{OUT}	DC Output Current, per Pin		± 25	mA
Icc	DC Supply Current, V_{CC} and GND Pir	ns	± 75	mA
P _D	Power Dissipation in Still Air	SOIC TSSOP	500 450	mW
T _{STG}	Storage Temperature Range		-65 to +150	°C
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	>2000 >200 >200	٧
I _{LATCHUP}	Latchup Performance	Above V _{CC} and Below GND at 125°C (Note 5)	±300	mA
θ_{JA}	Thermal Resistance, Junction-to-Am	bient SOIC TSSOP	96 128	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.
 Tested to EIA/JESD22-A114-A
- 3. Tested to EIA/JESD22-A115-A
- 4. Tested to JESD22-C101-A
- 5. Tested to EIA/JESD78

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics		Min	Max	Unit
V _{CC}	DC Supply Voltage		2.0	5.5	V
V _{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage		0	V _{CC}	V
T _A	Operating Temperature Range, all Package Types		-55	125	°C
t _r , t _f	Input Rise or Fall Time	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

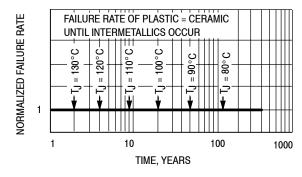


Figure 2. Failure Rate vs. Time Junction Temperature

DC CHARACTERISTICS (Voltages Referenced to GND)

			V _{CC}	1	Γ _A = 25°(2	T _A ≤	85°C	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V _{IH}	Minimum High-Level		_2.0	1 <u>.5</u>		_	_1.5_	1 <u>.5</u>	1.5		V
	Input Voltage		3.0 to 5.5	V _{CCX} 0.7			V _{CCX} 0.7	V _{CCX} 0.7	V _{CCX} 0.7		
V_{IL}	Maximum Low-Level		2.0			0.5		0.5		0.5	V
	Input Voltage		3.0 to 5.5			V _{CCX} 0.3		V _{CCX} 0.3		V _{CCX} 0.3	
V _{OH}	Maximum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -4 \text{ mA}$ $I_{OH} = -8 \text{ mA}$	3.0 4.5	2.58 3.94			2.48 3.8		2.34 3.66		
V _{OL}	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50 \mu\text{A}$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = 4 \text{ mA}$ $I_{OH} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μΑ
I _{OZ}	Maximum 3-State Leakage Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	5.5			±0.25		±2.5		±2.5	μΑ
I _{CC}	Maximum Quiescent Supply Current (per package)	$V_{IN} = V_{CC}$ or GND	5.5			4.0		40.0		40.0	μΑ

AC ELECTRICAL CHARACTERISTICS (Input $t_f = t_f = 3.0 \text{ ns}$)

	T _A = 25°C		T _A ≤ 85°C		-55°C ≤ T _A ≤ 125°C					
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, A to YA or	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		5.8 8.3	8.4 11.9	1.0 1.0	10.0 13.5	1.0 1.0	11.0 14.5	ns
	B to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ pF}$ $C_L = 50 \text{ pF}$		3.9 5.4	5.5 7.5	1.0 1.0	6.5 8.5	1.0 1.0	7.5 9.5	
t _{PZL} , t _{PZH}	Output Enable Time OEA to YA or	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{ pF}$ $R_L = 1 \text{ k}\Omega$ $C_L = 50 \text{ pF}$		6.6 9.1	10.6 14.1	1.0 1.0	12.5 16.0	1.0 1.0	13.5 17.0	ns
	OEB to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15 \text{ pF}$ $R_L = 1 \text{ k}\Omega$ $C_L = 50 \text{ pF}$		4.7 6.2	7.3 9.3	1.0 1.0	8.5 10.5	1.0 1.0	9.5 11.5	
t _{PLZ} , t _{PHZ}	Output Disable Time OEA to YA or	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 50 \text{ pF}$ $R_L = 1 \text{ k}\Omega$		10.3	14.0	1.0	16.0	1.0	17.0	ns
	OEB to YB	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 50 \text{ pF}$ $R_L = 1 \text{ k}\Omega$		6.7	9.2	1.0	10.5	1.0	11.5	
t _{OSLH} , t _{OSHL}	Output to Output Skew	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 50 \text{ pF}$ (Note 6)			1.5		1.5		1.5	ns
		$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 50 \text{ pF}$ (Note 6)			1.0		1.0		1.5	
C _{in}	Maximum Input Capacitance			4	10		10		10	pF
C _{out}	Maximum Three-State Output Capacitance (Output in High-Impedance State)			6						pF

		Typical @ 25°C, V _{CC} = 5.0V	
C_{PD}	Power Dissipation Capacitance (Note 7)	19	pF

^{6.} Parameter guaranteed by design. $t_{OSLH} = |t_{PLHm} - t_{PLHn}|$, $t_{OSHL} = |t_{PHLm} - t_{PHLn}|$.

NOISE CHARACTERISTICS (Input $t_r = t_f = 3.0$ ns, $C_L = 50$ pF, $V_{CC} = 5.0$ V)

		T _A = 25°C		
Symbol	Parameter	Тур	Max	Unit
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.6	0.9	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.6	-0.9	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

^{7.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/8 (per bit). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

SWITCHING WAVEFORMS

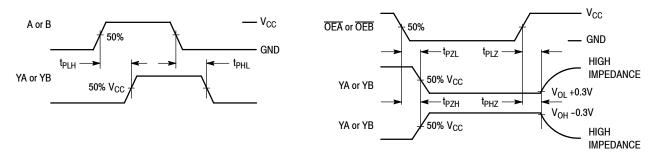


Figure 3. Switching Waveform

Figure 4. Switching Waveform

TEST CIRCUITS

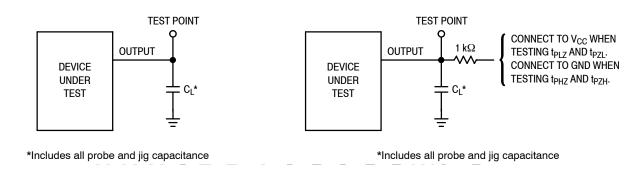


Figure 5. Test Circuit

Figure 6. Test Circuit

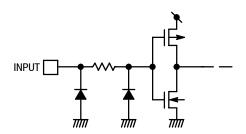
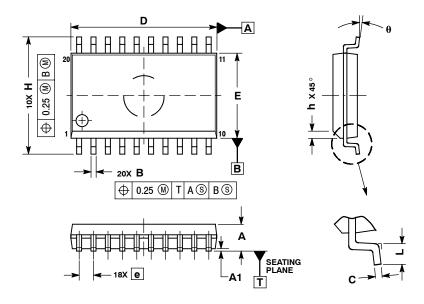


Figure 7. Input Equivalent Circuit

OUTLINE DIMENSIONS

SOIC-20 WB **DW SUFFIX** CASE 751D-05 **ISSUE G**



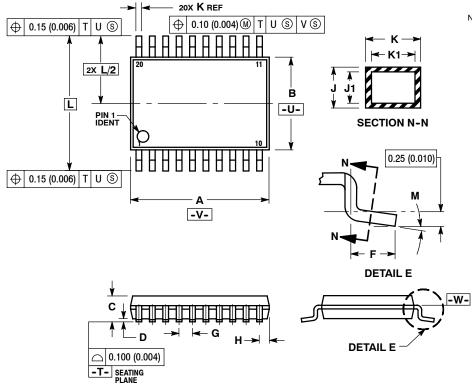
- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
- INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
- 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

MAXIMUM MUDEL PROTROSION U. 15 PER 31M DIMENSION B DOES NOT INCLUDE DAMBAR PROTRUSION ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS				
DIM	MIN	MAX			
Α	2.35	2.65			
A1	0.10	0.25			
В	0.35	0.49			
С	0.23	0.32			
D	12.65	12.95			
Е	7.40	7.60			
е	1.27	BSC			
Н	10.05	10.55			
h	0.25	0.75			
L	0.50	0.90			
θ	0 °	7 °			

TSSOP-20 **DT SUFFIX** CASE 948E-02

ISSUE B



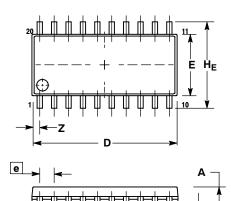
NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION:
- MILLIMETER.
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- SIDE.
 DIMENSION B DOES NOT INCLUDE
 INTERLEAD FLASH OR PROTRUSION.
 INTERLEAD FLASH OR PROTRUSION
 SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50 0.75		0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252	BSC	
M	0°	8°	0°	8°	

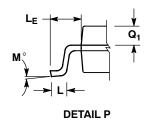
OUTLINE DIMENSIONS

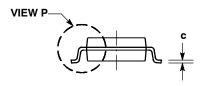
SOIC EIAJ-20 M SUFFIX CASE 967-01 ISSUE O



0.10 (0.004)

⊕ 0.13 (0.005) M





NOTES:

- VOIES:

 1. DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD
 FLASH OR PROTRUSIONS AND ARE MEASURED
 AT THE DROTTED LINE MOLD ET AS HEAD AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006)
- PER SIDE.

 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.

 5. THE LEAD WIDTH DIMENSION (b) DOES NOT
- INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH
 DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
С	0.18	0.27	0.007	0.011
D	12.35	12.80	0.486	0.504
E	5.10	5.45	0.201	0.215
е	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0 °	10°	0 °	10°
Q ₁	0.70	0.90	0.028	0.035
Z		0.81		0.032

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